Title (en)

METHOD FOR OPTIMISING THE ETCH RATE OF A POLYCRYSTALLINE LAYER

Title (de)

METHODE ZUR OPTIMIERUNG DER ÄTZGESCHWINDIGKEIT EINER POLYKRISTALLINEN SCHICHT

Title (fr)

METHODE D'OPTIMISATION DE LA VITESSE DE GRAVURE D'UNE COUCHE POLYCRISTALLINE

Publication

EP 1027726 A1 20000816 (FR)

Application

EP 98938607 A 19980605

Priority

- EP 98938607 A 19980605
- EP 9803391 W 19980605
- EP 97111826 A 19970711

Abstract (en)

[origin: EP0890979A1] The invention concerns a method for optimising the etch rate of a polycrystalline layer having a predetermined composition of at least two chemical types arranged in granular form and grain boundaries, said layer being produced in a semiconductor substrate by a deposit process whereof the parameters are to be determined, and to be etched by a reactive agent capable of reacting with the type constituting the major part in the layer. Said method defines a structure parameter representing the density of the layer grain boundaries, said parameter being equal to the grain boundaries total length per unit area. Said method comprises a step consisting in determining the least value of the structure parameter among the different layer samples having the predetermined composition, said value corresponding to deposit parameter values which optimise the etch rate.

IPC 1-7

H01L 21/3205; H01L 21/285; C23C 14/58; H01L 21/3213

IPC 8 full level

H01L 21/302 (2006.01); **C23C 14/58** (2006.01); **H01L 21/285** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/3213** (2006.01)

CPC (source: EP KR US)

C23C 14/58 (2013.01 - EP US); **H01L 21/28518** (2013.01 - EP US); **H01L 21/3213** (2013.01 - KR); **H01L 21/32137** (2013.01 - EP US)

Citation (search report)

See references of WO 9903142A1

Designated contracting state (EPC)

AT BE CH DE FR GB IE LI NL

DOCDB simple family (publication)

EP 0890979 A1 19990113; EP 1027726 A1 20000816; JP 2001510280 A 20010731; KR 20010021638 A 20010315; TW 405180 B 20000911; US 6242325 B1 20010605; WO 9903142 A1 19990121

DOCDB simple family (application)

EP 97111826 A 19970711; EP 9803391 W 19980605; EP 98938607 A 19980605; JP 2000502534 A 19980605; KR 20007000196 A 20000108; TW 87111255 A 19980713; US 46228500 A 20000209